HALL DEVICE BIASING CIRCUIT AND

MAGNETISM DETECTION CIRCUIT INCLUDING THE SAME

BACKGROUND OF THE INVENTION

1. FIELD OF THE INVENTION:

The present invention relates to a Hall device biasing circuit for applying a bias voltage to each of at least two Hall devices, and a magnetism detection circuit including the same.

2. DESCRIPTION OF THE RELATED ART:

A Hall device is used for magnetism detection in a wide range of fields including motor driving circuits, pickup control of optical disks and the like, focusing control of cameras, and TPS mounted on automobiles and the like.

Figure 6 shows an operating principle of a Hall device. When a magnetic field having magnetic flux density B is applied to a Hall device 41, the Hall device 41 outputs a voltage V_H in proportion to the applied magnetic flux density B.

Systems for driving a plurality of Hall devices are classified into a constant current driving system for supplying a constant current to drive the Hall devices

(in which the Hall devices are connected in series) and a constant voltage driving system for applying a constant voltage to drive the Hall devices (in which the Hall devices are connected in parallel).

Figure **7** shows a practical example of a constant voltage driving system for driving a plurality of Hall devices **41a** through **41o** connected in parallel. Figure **8** shows a practical example of a constant current driving system for driving a plurality of Hall devices **41a** through **41o** connected in series.

The constant voltage driving system shown in Figure **7** operates in the following manner. A constant voltage is applied to each of the Hall devices **41a**, **41b**, and **41o** connected in parallel from a constant voltage source **42**. Then, signal output terminals $H1^+$ and $H1^-$ of the Hall device **41a**, signal output terminals $H2^+$ and $H2^-$ of the Hall device **41b**, and signal output terminals $H3^+$ and $H3^-$ of the Hall device **41o** each output a voltage in proportion to a magnetic flux density applied to each of the Hall devices **41a**, **41b** and **41o**.

According to this system, the Hall devices **41a**,

41b and **41c** are each driven at a constant voltage.

The constant current driving system shown in Figure **8** for driving the Hall devices **41a**, **41b**, and **41c** connected in series is disclosed in, for example, Japanese Laid-Open Publication No. 9-65682. A voltage from a motor driving circuit **43** is applied to the Hall devices **41a**, **41b**, and **41c**, and the Hall devices **41a** through **41c** are each driven by a constant current. Accordingly, even when the number of Hall devices is increased or decreased, the driving current of the entire driving circuit does not change much.

An output voltage V_H of the Hall device driven by the constant current driving system is represented by expression (1), and an output voltage V_H of the Hall device driven by the constant voltage driving system is represented by expression (2).

$$V_H = (RH/d) \cdot Ic \cdot B \quad \ldots \ldots \quad (1)$$
$$V_H = \mu H \cdot (W/L) \cdot Vin \cdot B \quad \ldots \ldots \quad (2)$$

In the expressions (1) and (2), B represents the magnetic flux density applied to the Hall device, d

represents the thickness of a magnetic field sensing portion in the Hall device (thickness of the Hall device), and W and L respectively represent the width and length of the magnetic field sensing portion in the Hall device

5   with respect to the driving voltage. Ic represents a driving current in the constant current driving system, and Vin is a driving voltage in the constant voltage driving system. In expression (1), RH represents a Hall coefficient of the Hall device and is represented by

10    $RH=1/(e \cdot n)$, where e is a charge amount of electrons, and n is a carrier concentration of the Hall device. In expression (2), μH is an electron mobility of a semiconductor in the Hall device.

15   It is now assumed that the magnetic flux density B is constant and the size of the magnetic field sensing portion of the Hall device is constant. By the constant current driving system, since the driving current Ic is constant, the output voltage V_H of the Hall device is in

20   proportion to the Hall coefficient RH based on expression (1). By the constant voltage driving system, since the driving voltage Vin is constant, the output voltage V_H of the Hall device is in proportion to the electron mobility μH based on expression (2). Generally, it is known that

the Hall coefficient RH is high in temperature dependency and that the electron mobility μH is low in temperature dependency.

5   The constant voltage driving system shown in Figure **7** provides better temperature characteristics than the constant current driving system, and thus the Hall devices **41a** through **41c** in Figure **7** each output a voltage which is stable against a change in the ambient 10 temperature.   However, the constant voltage driving system requires a driving current in proportion to the number of Hall devices used, and thus has a disadvantage in that when a great number of Hall devices are used, the current consumption cannot be suppressed. This can be 15 a very serious problem in a circuit having an especially large number of Hall devices due to the significant increase in the current consumption.

By the constant current driving system shown in 20 Figure **8**, a driving current provided by the motor driving circuit **43** as a power source is used sequentially for the Hall devices **41a** through **41c** which are connected in series. Accordingly, even when the number of Hall devices is increased, the amount of the driving current passing

through the Hall devices is not increased. However, in such a case, the problem that the temperature dependency is raised as described above.

SUMMARY OF THE INVENTION

According to one aspect of the invention, a Hall device biasing circuit includes a plurality of terminals for applying a bias voltage to a plurality of Hall devices connected in series, respectively.

In one embodiment of the invention, the Hall device biasing circuit further includes a constant voltage supply section for supplying a constant bias voltage to each of the plurality of terminals.

In one embodiment of the invention, the constant voltage supply section includes a constant voltage supply circuit in correspondence to the plurality of Hall devices.

In one embodiment of the invention, the constant voltage supply section includes: a constant voltage supply circuit, at least one current path through which

a bias correction current flows from one of the plurality of terminals to another of the plurality of terminals, and a correction current supply section for selecting one of the at least one current path based on a current amount

5   therein and adjusting the current amount in the selected current path to supply the bias correction current.

In one embodiment of the invention, the correction current supply section includes: a constant voltage

10   generation circuit, and a comparison section connected to the at least one current path for selecting one of the at least one current path based on a current amount therein and adjusting the current amount in the selected current path based on a current amount flowing through the at least

15   one current path and a current amount generated in the constant voltage generation circuit.

In one embodiment of the invention, the constant voltage supply section uses a supply voltage outside the

20   Hall device biasing circuit.

In one embodiment of the invention, the constant voltage supply section includes: at least one current path through which a bias correction current flows from one

of the plurality of terminals to another of the plurality
of terminals, and a correction current supply section for
selecting one of the at least one current path based on
a current amount therein and adjusting the current amount
5   in the selected current path to supply the bias correction
current.

In one embodiment of the invention, the correction
current supply section includes: a reference voltage
10   source, and a comparison section connected to the at least
one current path for selecting one of the at least one
current path based on a current amount therein and
adjusting the current amount in the selected current path
based on a current amount flowing through one of the
15   plurality of terminals and a current amount generated in
the reference voltage source.

In one embodiment of the invention, the comparison
section includes a comparator circuit.

20

In one embodiment of the invention, a positive
terminal of the comparator circuit is connected to a
terminal of one of the plurality of terminals, and the
negative terminal of the comparator circuit is supplied

with a reference voltage generated in the reference voltage source.

In one embodiment of the invention, the comparator circuit includes a buffer amplifier.

In one embodiment of the invention, the at least one current path includes a switching device.

In one embodiment of the invention, the at least one current path includes an OR circuit and an inverter.

In one embodiment of the invention, the correction current supply section includes: a plurality of reference voltage sources respectively provided in correspondence to the plurality of Hall devices, and a plurality of comparison sections each connected to each of the at least one current path for selecting one of the at least one current path based on a current amount therein and adjusting the current amount in the selected current path based on a current amount flowing through one of the plurality of terminals and a current amount generated in one of the plurality of reference voltage sources corresponding to the one of the plurality of terminals.

In one embodiment of the invention, the correction current supply section further includes a resistor between the reference voltage source and the comparison section for dividing a resistance of the reference voltage source.

In one embodiment of the invention, a former-stage terminal with respect to one of the plurality of terminals corresponding to the buffer amplifier is connected to a positive power supply of the buffer amplifier, and a latter-stage terminal with respect to the one of the plurality of terminals corresponding to the buffer amplifier is connected to a negative power supply of the buffer amplifier.

According to another aspect of the invention, a magnetism detection circuit includes a plurality of Hall devices connected in series; and a Hall device biasing circuit including at least a plurality of terminals corresponding to the plurality of Hall devices for supplying a constant bias voltage to each of the plurality of Hall devices respectively from the plurality of terminals.

In one embodiment of the invention, the Hall device biasing circuit further includes a constant voltage supply section.

5

In one embodiment of the invention, one end of the series of plurality of Hall devices is grounded.

Thus, the invention described herein makes

10 possible the advantages of providing a Hall device biasing circuit for driving each of a plurality of Hall devices so as to maintain the satisfactory temperature dependency without increasing the driving current even when the number of Hall devices is increased, and a magnetism

15 detection circuit including such a Hall device biasing circuit.

These and other advantages of the present invention will become apparent to those skilled in the

20 art upon reading and understanding the following detailed description with reference to the accompanying figures.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a block diagram illustrating a Hall device biasing circuit in one example according to the present invention;

Figure 2 is a block diagram illustrating a Hall device biasing circuit in another example according to the present invention;

Figure 3 is a block diagram illustrating a Hall device biasing circuit in still another example according to the present invention;

Figure 4 is a block diagram illustrating a Hall device biasing circuit in a modification of the example shown in Figure 3;

Figure 5 is a block diagram illustrating a Hall device biasing circuit in still another example according to the present invention;

Figure 6 illustrates the operating principle of a Hall device;

Figure **7** is a block diagram illustrating a conventional Hall device biasing circuit; and

5   Figure **8** is a block diagram illustrating another conventional Hall device biasing circuit.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

10   Hereinafter, the present invention will be described by way of illustrative examples with reference to the accompanying drawings.

(Example 1)

15   Figure **1** is a block diagram of a Hall device biasing circuit **100** and a magnetism detection circuit **150** in a first example according to the present invention. The magnetism detection circuit **150** includes the Hall device biasing circuit **100**, a first Hall device **1**, a second

20   Hall device **2** and a third Hall device **3**. The first Hall device **1**, the second Hall device **2** and the third Hall device **3** are connected in series.

The Hall device biasing circuit **100** includes a

constant voltage supply section **180** for applying a bias voltage to each of the Hall devices **1** through **3**. One end of the third Hall device **3** is grounded. The Hall device biasing circuit **100** further includes a first terminal **4**, a second terminal **5** and a third terminal **6** all for applying a bias voltage. In this specification, a terminal which is closer to the first terminal **4**, namely, closer to a supply voltage V_{CC}, than a particular terminal will be referred to as the "former-stage terminal" with respect to the particular terminal. The "former-stage terminal" is not limited to a terminal which is immediately before the particular terminal. A terminal which is farther from the first terminal **4** than the particular terminal will be referred to as the "latter-stage terminal" with respect to the particular terminal. The "latter-stage terminal" is not limited to a terminal which is immediately after the particular terminal. In the first example, the first terminal **4** is a "former-stage terminal" with respect to the second terminal **5**, and the third terminal **6** is a "latter-stage terminal" with respect to the second terminal **5**.

The first terminal **4** is connected to the first Hall device **1**, the second terminal **5** is connected to a

connection point between the first Hall device **1** and the second Hall device **2**, and the third terminal **6** is connected to a connection point between the second Hall device **2** and the third Hall device **3**. The Hall device **1** has signal output terminals **1a** and **1b**. The Hall device **2** has signal output terminals **2a** and **2b**. The Hall device **3** has signal output terminals **3a** and **3b**. A current which is in proportion to the magnetic flux density applied to each of the Hall devices **1**, **2** and **3** is output from the corresponding signal output terminal (terminals **1a** and **1b**, **2a** and **2b**, **3a** and **3b**).

The constant voltage supply section **180** includes a first constant voltage supply circuit **107**, a second constant voltage supply circuit **108**, and a third constant voltage supply circuit **109**, which are each supplied with a prescribed supply voltage V_{cc}. The supply voltage V_{cc} is located outside the Hall device biasing circuit **100** in Figure **1**, but can be included in the Hall device biasing circuit **100**. The supply voltage V_{cc} is connected to each of the first constant voltage supply circuit **107**, the second constant voltage supply circuit **108**, and the third constant voltage supply circuit **109**. The first constant voltage supply circuit **107**, the second constant voltage

supply circuit **108**, and the third constant voltage supply circuit **109** are each grounded. The first constant voltage supply circuit **107**, the second constant voltage supply circuit **108**, and the third constant voltage supply circuit **109** output currents I_1, I_2 and I_3 through the first terminal **4**, the second terminal **5** and the third terminal **6**, respectively, so as to apply a constant voltage to the first Hall device **1**, the second Hall device **2**, and the third Hall device **3**, respectively. In the first example, since the current is shared by the first through third Hall devices **1** through **3** by connecting the first through third Hall devices **1** through **3** in series, the current consumption is suppressed. Therefore, a voltage of the first terminal **4** is set to be lower than the supply voltage V_{cc} by the first constant voltage supply circuit **107**, a voltage of the second terminal **5** is set to be lower than the voltage of the first terminal **4** by the second constant voltage supply circuit **108**, and a voltage of the third terminal **6** is set to be lower than the voltage of the second terminal **5** by the third constant voltage supply circuit **109**.

The current I_1 output from the first terminal **4** is supplied to a bias application terminal of the first

Hall device 1, a current I_2 output from the second terminal 5 is supplied to a bias application terminal of the second Hall device 2, and a current I_3 output from the third terminal 6 is supplied to a bias application terminal of

5   the third Hall device 3. Due to this structure, the first through third Hall devices 1 through 3 are provided with constant bias voltages supplied from the first through third constant voltage supply circuits 107, 108 and 109, respectively.

10

As described above, the first through third Hall devices 1 through 3 are each supplied with a constant voltage. Thus, the output voltages V_H of the first through third Hall devices 1 through 3 are represented

15   by expression (2) by the constant voltage driving system set forth above.

$$V_H = \mu H \cdot (W/L) \cdot Vin \cdot B \ \ldots \ldots \ (2)$$

20   According to the structure of the first example, the output voltage V_H is in proportion to the electron mobility μH having a low temperature dependency despite that the first through third Hall devices 1 through 3 are connected in series. Thus, the first through third Hall

devices **1** through **3** provide output voltages which are stable against a temperature change. In other words, the Hall devices **1** through **3** operate with satisfactory temperature characteristics.

(Example 2)

Figure **2** is a block diagram of a Hall device biasing circuit **200** and a magnetism detection circuit **250** in a second example according to the present invention. The magnetism detection circuit **250** includes the Hall device biasing circuit **200**, a first Hall device **1**, a second Hall device **2** and a third Hall device **3**. The first Hall device **1**, the second Hall device **2** and the third Hall device **3** are connected in series.

The Hall device biasing circuit **200** includes a constant voltage supply section **280**. The constant voltage supply section **280** includes a constant voltage supply circuit **207**, and a first correction current supply section **215** and a second correction current supply section **216** both for generating a bias correction current. The first correction current supply section **215** includes a first constant voltage generation circuit **208a** for generating a prescribed constant voltage and a first

comparison section **210a**. The second correction current supply section **216** includes a first constant voltage generation circuit **208b** for generating a prescribed constant voltage and a second comparison section **210b**. In the second example, a comparator circuit is used for each of the first and second comparison sections **210a** and **210b**. The constant voltage supply circuit **207** supplies a bias voltage to the first Hall device **1** among the three Hall devices **1** through **3** connected in series. One end of the third Hall device **3** is grounded. The Hall device biasing circuit **200** further includes a first terminal **4**, a second terminal **5**, a third terminal **6**, and a ground terminal **13**. The first terminal **4**, the second terminal **5**, and the third terminal **6** respectively apply a bias voltage to the Hall devices **1**, **2** and **3**. The ground terminal **13** is connected to the ground. The first terminal **4** is connected to the first Hall device **1**, the second terminal **5** is connected to a connection point between the first Hall device **1** and the second Hall device **2**, and the third terminal **6** is connected to a connection point between the second Hall device **2** and the third Hall device **3**.

Currents output from the terminals **4** through **6** and

13 are referred to as I_{o1} through I_{o4}, respectively. Currents input to the terminals **4** through **6** are referred to as I_{11} through I_{13}.

5   The constant voltage supply circuit **207** is connected to the first terminal **4** through a line **221**. The first comparison section **210a** is connected to the second terminal **5** through a line **222**. The second comparison section **210b** is connected to the third terminal **6** through

10 a line **223**.

        The first current path **212a** is provided between the lines **221** and **222**, and the second current path **212b** is provided between the lines **222** and **223**. The line **222**

15 through which the current I_{12} input to the second terminal **5** or current I_{o2} output from the second terminal **5** flows is connected to the first comparison section **210a**, and the first comparison section **210a** is supplied with a current generated in the first constant voltage

20 generation circuit **208a**. Based on the output from the first comparison section **210a**, the first current path **212a** or the second current path **212b** is selected, and the amount of the current flowing in the selected current path **212a** or **212b** is adjusted as described in detail below.

A third current path **212c** is provided between the lines **222** and **223**, and a fourth current path **212d** is provided between the lines **223** and the ground terminal

5   **13**.   The line **223** through which the current I_{i3} input to the third terminal **6** or the current I_{o3} output from the third terminal **6** flows is connected to the second comparison section **210b**, and the second comparison section **210b** is supplied with a current generated in the

10   second constant voltage generation circuit **208b**.   Based on the output from the second comparison section **210b**, the third current path **212c** or the fourth current path **212d** is selected, and the amount of the current flowing in the selected current path **212c** or **212d** is adjusted as

15   described in detail below.

The first comparison section **210a** compares the current I_{i2} input to the second terminal **5** or the current I_{o2} output from the second terminal **5** with the current from

20   the first constant voltage generation circuit **208a**.   When a driving current I_{H2} for the second Hall device **2** is insufficient, the first comparison section **210a** selects the first current path **212a** and supplies a portion of the current which is to be supplied to the first Hall device

1 to the second Hall device 2 through the second terminal
5 as a bias correction current. When the driving current
I_{H2} for the second Hall device 2 is excessive, the first
comparison section 210a selects the second current path
5   212b and supplies an excessive portion of the current
which is to be supplied to the second Hall device 2 to
the third Hall device 3 through the third terminal 6 as
a bias correction current.

10   Similarly, the second comparison section 210b
compares the current I_{i3} input to the third terminal 6 or
the current I_{o3} output from the third terminal 6 with the
current from the second constant voltage generation
circuit 208b. When a driving current I_{H3} for the third
15   Hall device 3 is insufficient, the second comparison
section 210b selects the third current path 212c and
supplies a portion of the current which is to be supplied
to the second Hall device 2 to the third Hall device 3
through the third terminal 6 as a bias correction current.
20   When the driving current I_{H3} for the third Hall device 3
is excessive, the second comparison section 210b selects
the fourth current path 212d and supplies an excessive
portion of the current which is to be supplied to the third
Hall device 3 to the ground through the ground terminal

13 as a bias correction current.

In general, Hall devices have different internal resistances on an individual basis, and the internal resistances are dispersed in the range of about 1.5 times to 2 times with respect to one another.

For example, it is assumed that in the magnetism detection circuit **250** shown in Figure **2**, the internal resistances of the Hall devices **1** through **3** are dispersed, and the internal resistance of the second Hall device **2** is twice the internal resistance of each of the first and third Hall devices **1** and **3**. In this case, in order to apply a voltage VR1 to the entirety of the three Hall devices **1** through **3** connected in series so that the bias voltage of each of the Hall devices **1** through **3** is VR1/3, the driving current flowing in each of the Hall devices **1** through **3** needs to have the following relationship.

$$I_{o1}=I_{H1}=2I_{H2}=I_{H3} \ \ldots\ldots\ (3)$$

In other words, in order to cause each of the Hall devices **1** through **3** having the above-mentioned internal resistances to have a constant voltage, the current

passing through the Hall device 2 needs to be half of the current passing through each of the Hall devices 1 and 3.

5   In order to cause a current I_{H2} to flow in the Hall device 2, the currents input to and output from the first through third terminals 4 through 6 in the Hall device biasing circuit 200 have the following relationships.

10      $$I_{H1} = I_{12} + I_{H2},$$
$$I_{H2} = I_{12} = I_{o3}, \quad \ldots \ldots \quad (4)$$
$$I_{H3} = I_{H2} + I_{o3}$$

      A current I_{H1} which has passed through the Hall
15 device 1 is divided into a current I_{12} input to the Hall device biasing circuit 200 through the second terminal 5 and a current I_{H2} passing through the second Hall device 2 (first expression of (4)). A current I_{H3} passing through the Hall device 3 is represented by the sum of the current
20 I_{H2} which has passed through the second Hall device 2 and a current I_{o3} output from the Hall device biasing circuit 200 through the third terminal 6 (third expression of (4)). In this case, when the current I_{H2}, the current I_{12} and the current I_{o3} are equal to one another (second expression

of (4)), the Hall devices **1** through **3** are each supplied with a constant voltage.

In order to realize this, the first comparison section **210a** selects the second current path **212b** and adjusts the amount of the current therein, and thus a portion of the current flowing from first Hall device **1** to the second Hall device **2** (having a larger internal resistance) is branched as a bias correction current I_{12}. The bias correction current I_{12} is output from the third terminal **6** as the current I_{o3} through the second current path **212b** and is supplied to the third Hall device **3**. As a result, the driving current for the second Hall device **2** is 1/2 of the driving current passing through each of the first and third Hall devices **1** and **3**. Thus, the voltage of each of the first through third Hall devices **1** through **3** is VR1/3.

In Figure **2**, a bias voltage setting section **211** (corresponding to the constant voltage supply circuit **109** in Figure **1**) includes the second constant voltage generation circuit **208b**, the second comparison section **210b**, the third current path **212c** and the fourth current path **212d**. Similarly, a bias voltage setting section **214**

(corresponding to the constant voltage supply circuit **108** in Figure **1**) includes the first constant voltage generation circuit **208a**, the first comparison section **210a**, the first current path **212a** and the second current path **212b**.

Due to the above-described structure, the insufficiency and excessiveness in the driving currents for the first through third Hall devices **1** through **3** are counteracted. In consequence, the driving current for the Hall device which has the smallest resistance, namely, consumes the largest amount of current among the Hall devices **1** through **3** connected in series is consumed by the entirety of the Hall devices **1** through **3**. The Hall devices **1** through **3** do not require any larger amount of current. In other words, in the Hall device biasing circuit **200** and the magnetism detection circuit **250**, when the Hall devices **1** through **3** having different internal resistances are each driven in the state of being connected in series, the total driving current required to drive all the Hall devices **1** through **3** is determined by the Hall devices used. Accordingly, it is not necessary to limit the order of connecting the Hall devices (locations of the Hall devices). This is also

true when a different number of Hall devices are connected.

The Hall device biasing circuit **200** and the magnetism detection circuit **250** in the second example will be compared with the Hall device biasing circuit **100** (Figure 1) and the magnetism detection circuit **150** in the first example. In the Hall device biasing circuit **100** having no current path between the output terminals (between the terminals **4** and **5** and between the terminals **5** and **6**), when the current flowing from the first Hall device **1** to the second Hall device **2** is excessive, the excessive portion of the current I_2 (corresponding to I_{12} in Figure 2; in this case, I_2 has a negative value) is input to the Hall device biasing circuit **100** through the second terminal **5** and then expelled to the ground through the constant voltage supply circuit **108**. When the current I_3 for the third Hall device **3** (corresponding to I_{o3} in Figure 2) is insufficient, the insufficient portion of the current is supplied from the supply voltage V_{cc} through the constant voltage supply circuit **109**.

Accordingly, in the case where the Hall device biasing circuit **100** includes the constant voltage supply

circuits 107 through 109 independent from one another as shown in Figure 1, driving of the Hall devices 1 through 3 requires a current supplied from the supply voltage V_{cc} to the third terminal 6 in addition to the driving current

5   I_1 from the constant voltage supply circuit 107. As a result, the total driving current for the Hall devices 1 through 3 may be about 1.5 times the total current required to drive the Hall devices 1 through 3 by the Hall device biasing circuit 200 shown in Figure 2.

10

In the structure shown in Figure 1 where current paths are not provided for connecting the terminals 4 and 5 or for connecting the terminals 5 and 6, a current other than the driving current I_1 for the Hall device may be

15   consumed. In the structure shown in Figure 2, the Hall device biasing circuit 200 does not require such an additional current and thus the current consumption can be reduced.

20   (Example 3)

Figure 3 is a block diagram of a Hall device biasing circuit 300 and a magnetism detection circuit 350 in a third example according to the present invention. The magnetism detection circuit 350 includes the Hall

device biasing circuit **300**, a first Hall device **1**, a second Hall device **2** and a third Hall device **3**. The first Hall device **1**, the second Hall device **2** and the third Hall device **3** are connected in series. As in the second example, the

5 Hall device biasing circuit **300** applies a constant bias voltage to each of the Hall devices **1** through **3**.

The Hall device biasing circuit **300** includes a first terminal **4**, a second terminal **5**, a third terminal

10 **6**, and a ground terminal **13**. The first terminal **4** is connected to the first Hall device **1**, the second terminal **5** is connected to a connection point between the first Hall device **1** and the second Hall device **2**, and the third terminal **6** is connected to a connection point between the

15 second Hall device **2** and the third Hall device **3**.

The Hall device biasing circuit **300** further includes a constant voltage supply section **380**. The constant voltage supply section **380** includes a first

20 correction current supply section **355**, a second correction current supply section **360**, and a third correction current supply section **365**. The first correction current supply section **355** includes a first reference voltage source **322** and a first buffer amplifier

314. The second correction current supply section **360** includes a second reference voltage source **323** and a second buffer amplifier **315**. The third correction current supply section **365** includes a third reference voltage source **324** and a third buffer amplifier **316**. Among the reference voltage sources **322** through **324**, the first reference voltage source **322** provides the highest voltage level, the second voltage source **323** provides the next highest voltage level, and the third reference voltage source **324** provides the lowest voltage level.

Output terminals of the reference voltage sources **322**, **323** and **324** are respectively connected to negative terminals of the buffer amplifiers **314**, **315** and **316**. The first, second and third terminals **4**, **5** and **6** are connected to positive terminals of the first through third buffer amplifiers **314**, **315** and **316**. In the third example, the buffer amplifiers are used as comparator circuits of a comparison section corresponding to the comparison sections **210a** and **210b** of the Hall device biasing circuit **200** in Figure 2.

An output terminal of the first buffer amplifier **314** is connected to a gate of a P-channel MOS transistor

317. A source of the P-channel MOS transistor 317 is connected to a supply voltage V_{cc}. A drain of the P-channel MOS transistor 317 is connected to the first terminal 4. The supply voltage V_{cc} can be provided inside or outside the Hall device biasing circuit 300.

An output terminal of the second buffer amplifier 315 is connected to a gate of a P-channel MOS transistor 318 and also to a gate of an N-channel MOS transistor 319. A source of the P-channel MOS transistor 318 is connected to the first terminal 4. A drain of the P-channel MOS transistor 318 is connected to the second terminal 5 and also to a drain of the N-channel MOS transistor 319. A source of the N-channel MOS transistor 319 is connected to the third terminal 6.

An output terminal of the third buffer amplifier 316 is connected to a gate of a P-channel MOS transistor 320 and also to a gate of an N-channel MOS transistor 321. A source of the P-channel MOS transistor 320 is connected to the second terminal 5. A drain of the P-channel MOS transistor 320 is connected to the third terminal 6 and also to a drain of the N-channel MOS transistor 321. A source of the N-channel MOS transistor 321 is connected

to the ground terminal **13**.   The P-channel MOS transistors **317, 318** and **320** and the N-channel MOS transistors **319** and **321** act as current paths.

5   The correspondence of the elements in Figures **2** and **3** will be described. The reference voltage source **322**, the first buffer amplifier **314** and the P-channel MOS transistor **317** in Figure **3** correspond to the constant voltage supply circuit **207** in Figure **2**. The second

10 reference voltage source **323** (Figure **3**) corresponds to the constant voltage generation circuit **208a** (Figure **2**). The second buffer amplifier **315** (Figure **3**) corresponds to the first comparison section **210a** (Figure **2**). The P-channel MOS transistor **318**, and the N-channel MOS

15 transistor **319** (Figure **3**) respectively correspond to the current paths **212a** and **212b** (Figure **2**). Similarly, the reference voltage source **324** (Figure **3**) corresponds to the constant voltage generation circuit **208b** (Figure **2**). The third buffer amplifier **316** (Figure **3**) corresponds to

20 the second comparison section **210b** (Figure **2**). The P-channel MOS transistor **320**, and the N-channel MOS transistor **321** (Figure **3**) respectively correspond to the current paths **212c** and **212d** (Figure **2**). As described above, switching devices such as, for example, MOS

transistors can be used as the current paths.

The Hall device biasing circuit **300** having the above-described structure operates, for example, as 5   follows.

The negative terminal of the first buffer amplifier **314** is supplied with an output voltage from the reference voltage source **322** as a reference voltage, and 10   the positive terminal of the first buffer amplifier **314** is supplied with a voltage of the first terminal **4** which has been fed back. When the voltage of the first terminal **4** becomes lower than the output voltage from the reference voltage source **322**, the output of the first buffer 15   amplifier **314** is lowered, and the voltage level of the gate of the P-channel MOS transistor **317** is also lowered, the gate being connected to the first buffer amplifier **314**. Thus, the current flowing in the P-channel MOS transistor **317** is increased and the voltage level of the 20   first terminal **4** is raised.

When the voltage of the first terminal **4** is raised to the voltage of the reference voltage source **322**, the output of the first buffer amplifier **314** is raised, and

the voltage level of the gate of the P-channel MOS transistor **317** is also raised. Thus, the voltage level of the terminal **4** is lowered. As a result, the voltage level of the first terminal **4** is maintained at the output

5   voltage level of the reference voltage source **322**.

Similarly, the positive terminal of the second buffer amplifier **315** is supplied with a voltage of the second terminal **5** which has been fed back, and the P-

10   channel MOS transistor **318** acts so as to maintain the voltage level of the second terminal **5** at the output voltage level of the second reference voltage source **323** as described below.

15   When the voltage of the second terminal **5** becomes lower than the output voltage from the second reference voltage source **323**, the output of the second buffer amplifier **315** is lowered, and the voltage level of the gate of the P-channel MOS transistor **318** is also lowered.

20   Thus, the current flowing in the P-channel MOS transistor **318** is increased and the voltage level of the second terminal **5** is raised. When the voltage of the second terminal **5** is raised to the voltage of the second reference voltage source **323**, the output of the second buffer

amplifier 315 is raised, and the voltage level of the gate
of the P-channel MOS transistor 318 is also raised. Thus,
the voltage level of the second terminal 5 is lowered.
As a result, the voltage level of the second terminal 5

5   is maintained at the output voltage level of the second
reference voltage source 323.

The output of the second buffer amplifier 315 is
supplied to the gate of the N-channel MOS transistor 319.

10   When the voltage level of the second terminal 5 is raised,
the output level of the second buffer amplifier 315 is
raised. Thus, the voltage level of the gate of the
N-channel MOS transistor 319 is raised, and the current
passing through the drain of the N-channel MOS transistor

15   319 is increased. As a result, the current in the second
terminal 5 flows through the N-channel MOS transistor 319,
and thus the output level of the second terminal 5 is
lowered. When the output level of the second terminal
5 is lowered down to the voltage level of the second

20   reference voltage source 323, the N-channel MOS
transistor 319 is turned off, and the voltage level of
the second terminal 5 is maintained at the voltage level
of the second reference voltage source 323.

Similarly, the voltage level of the third terminal 6 is also maintained at the voltage level of the third reference voltage source 324 by turning on or off the P-channel MOS transistor 320 and the N-channel MOS transistor 321 based on the output of the third buffer amplifier 316.

All the Hall devices 1 through 3 are driven by a current I_{o1} supplied from the first terminal 4, and the voltage level of the first terminal 4 is maintained at the voltage level of the first reference voltage source 322. The voltage level of the second terminal 5 is maintained at a constant level by the P-channel MOS transistor 318 and the N-channel MOS transistor 319. When the current is insufficient at the second terminal 5, a current I_{11} from the first terminal 4 is supplied to the second terminal 5 as a bias correction current I_{o2}. When the current is excessive at the second terminal 5, the bias correction current I_{12} is output from the second terminal 5. Similarly, the voltage level of the third terminal 6 is maintained at a constant level by the P-channel MOS transistor 320 and the N-channel MOS transistor 321.

As described above, the voltage level of each of the second terminal **5** and the third terminal **6** can be adjusted by a simple circuit configuration obtaining by combining a pair of transistors and a buffer amplifier

5   supplied with a reference voltage by a reference voltage source. The circuit can be easily designed.

In the above structure, the current passing through one output terminal (terminals **4**, **5** or **6**) is

10   adjusted by two transistors. As can be appreciated from the above, there is no undesirable possibility that the transistor will operate simultaneously to cause a shoot-through current to flow and thus to increase the current consumption.

15

In the above structure, MOS transistors are used. A similar effect is obtained by a bipolar circuit including a PNP transistor instead of the P-channel MOS transistor and an NPN transistor instead of the N-channel

20   MOS transistor.

Figure **4** is a block diagram of a Hall device biasing circuit **400** and a magnetism detection circuit **450** in a modification of the third example according to the

present invention.

In the Hall device biasing circuit **300** shown in Figure **3**, the N-channel MOS transistor **319** and the P-channel MOS transistor **320** are provided on one current path between the second terminal **5** and the third terminal **6**. In the Hall device biasing circuit **400** shown in Figure **4**, one N-channel MOS transistor **419** can be provided on the current path between the second terminal **5** and the third terminal **6**. In this structure, an output signal from a second buffer amplifier **415** and a signal obtained by inverting an output signal from a third buffer amplifier **416** by an inverter **426** are synthesized by an OR (logical sum) circuit **425**, and the output from the OR circuit **425** is output to a gate of the N-channel MOS transistor **419** as a control signal, so that the current path between the terminals **5** and **6** is turned on and off by the N-channel MOS transistor **419**. Thus, the Hall device biasing circuit **400** in Figure **4** achieves a similar effect to that of the Hall device biasing circuit **300** in Figure **3**. The OR circuit **425** and the inverter **426** act as a current path.

In this case, an N-channel MOS transistor (not

shown) can be provided on a current path between the second

terminal **5** and the third terminal **6**, so that the output

signal from the second buffer amplifier **415** is inverted

by an inverter and output to the OR circuit **425** and also

5   the output signal from the third buffer amplifier **416** is

directly input to the OR circuit **425**.

     Such a structure is also applicable even when a

large number of current paths are required to drive a large

10   number of Hall devices. In this manner, the Hall device

biasing circuit can be reduced in size since the number

of transistors, for the current path, which need a large

space can be reduced.

15   (Example 4)

     Figure **5** is a block diagram of a Hall device

biasing circuit **500** and a magnetism detection circuit **550**

in a fourth example according to the present invention.

The Hall device biasing circuit **500** includes a constant

20   voltage supply section **580**. The constant voltage supply

section **580** includes a correction current supply section

555. The correction current supply section **555** includes

one reference voltage source **522** and three resistors **525**,

526 and **527** connected in series, instead of the three

reference voltage sources **322, 323** and **324** in the Hall device biasing circuit **300** (Figure **3**). The correction current supply section **555** further includes first, second and third buffer amplifiers **514, 515** and **516**. The voltage

5   of the reference voltage source **522** is divided by the resistors **525, 526** and **527**, and the divided voltages are respectively supplied to negative terminals of the buffer amplifiers **514, 515** and **516** as reference voltages. Due to such a structure, even when the number of Hall devices

10   is increased, it is not necessary to prepare an equal number of reference voltage sources to the number of the Hall devices. Thus, enlargement of the circuit scale and increase in the current consumption can be suppressed. Positive terminals of the buffer amplifiers **514, 515** and

15   **516** are respectively connected to the terminals **4, 5** and **6**. Therefore, the terminals **4** through **6** are respectively supplied with a voltage in the vicinity of the reference voltage supplied to the corresponding buffer amplifiers **514, 515** and **516**.

20

As a supply voltage for the buffer amplifiers **514, 515** and **516**, the voltage between the supply voltage V_{cc} and the ground is not necessary. As a supply voltage for the first buffer amplifier **514**, a voltage between the

supply voltage V_{cc} and the second terminal **5** is applied.
As a supply voltage for the second buffer amplifier **515**,
a voltage between the second terminal **5** and the third
terminal **6** is applied.   As a supply voltage for the third

5   buffer amplifier **516**, a voltage between the third terminal
6 and a ground terminal **13** is applied.

That is, a former-stage terminal with respect to
a terminal corresponding to a buffer amplifier is
10   connected to a positive power supply terminal of the
buffer amplifier, and a latter-stage terminal with
respect to the terminal corresponding to the buffer
amplifier is connected to a negative power supply terminal
of the buffer amplifier. Specifically, in Figure 5, a
15   positive power supply terminal **531** of the first buffer
amplifier **514** corresponding to a terminal **4** is connected
to the supply voltage V_{cc}, and a negative power supply
terminal **532** of the first buffer amplifier **514** is
connected to a second terminal **5**.   Here, the supply
20   voltage V_{cc} corresponds to the former-stage terminal with
respect to the first terminal **4**. A positive power supply
terminal **533** of the second buffer amplifier **515**
corresponding to the second terminal **5** is connected to
the first terminal **4**, and a negative power supply terminal

534 of the second buffer amplifier 515 is connected to a third terminal 6. A positive power supply terminal 535 of the third buffer amplifier 516 is connected to the second terminal 5, and a negative power supply terminal

5   536 of the third buffer amplifier 516 is connected to the ground terminal 13.

Accordingly, the current consumption in the buffer amplifiers 514, 515 and 516 can be reduced. Such

10   a structure is applicable even when a large number of buffer amplifiers are required to drive a large number of Hall devices.

As described above, a Hall device biasing circuit

15   according to the present invention includes a plurality of output terminals respectively for driving a plurality of Hall devices connected in series at a constant voltage. Since each of the Hall devices can be driven at a constant voltage, even when the number of Hall devices increases,

20   the total driving current required to drive all the Hall devices can be prevented from increasing. Moreover, each Hall device operates with satisfactory temperature characteristics.

In the case where a current path is provided between output terminals, the total current consumption of all the Hall devices can be further reduced. Regardless of the number of Hall devices, the consumed current is the current consumed only by the device consuming the highest amount of current among all the Hall devices. Accordingly, no problem arises even when the driving currents for the Hall devices are different from one another.

When buffer amplifiers are used to maintain the constant voltage, the current consumption in each buffer amplifier can be suppressed by connecting the power supply terminals thereof in series in the order of voltage level. The current consumption does not rely on the number of buffer amplifiers used.

Various other modifications will be apparent to and can be readily made by those skilled in the art without departing from the scope and spirit of this invention. Accordingly, it is not intended that the scope of the claims appended hereto be limited to the description as set forth herein, but rather that the claims be broadly construed.